

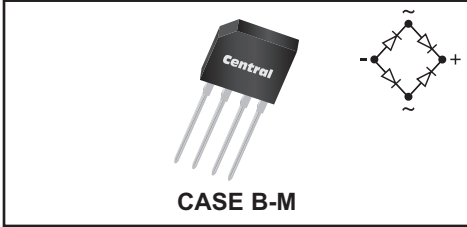
3N247-M SERIES
SILICON BRIDGE RECTIFIERS



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR 3N247-M series types are silicon single phase, full wave bridge rectifiers designed for general purpose applications.



MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

		3N <u>247-M</u>	3N <u>248-M</u>	3N <u>249-M</u>	3N <u>250-M</u>	3N <u>251-M</u>	3N <u>252-M</u>	UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	100	200	400	600	800	1000	V
DC Blocking Voltage	V_R	100	200	400	600	800	1000	V
RMS Reverse Voltage	$V_{R(RMS)}$	70	140	280	420	560	700	V
Average Forward Current ($T_A=75^{\circ}\text{C}$)	I_O				1.5			A
Peak Forward Surge Current	I_{FSM}				30			A
Operating and Storage Junction Temperature	T_J, T_{stg}				-65 to +150			$^{\circ}\text{C}$

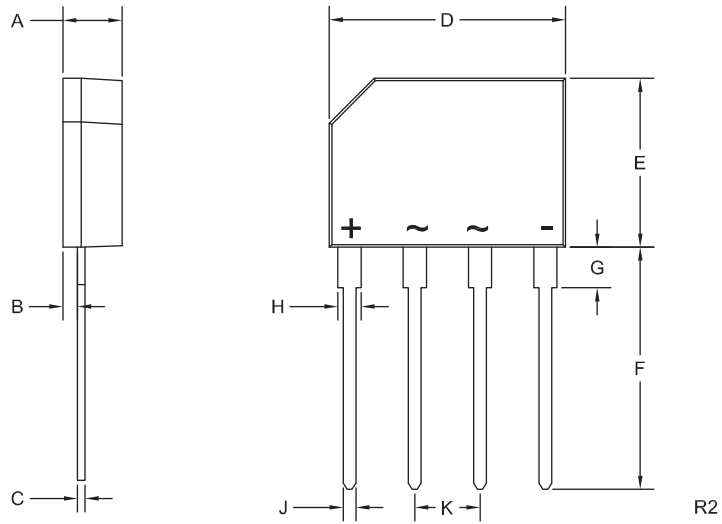
ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_R	$V_R=\text{Rated } V_{RRM}$		10	μA
V_F	$I_F=3.14\text{A}$		1.3	V

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CASE B-M - MECHANICAL OUTLINE



MARKING:
FULL PART NUMBER

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.132	0.144	3.35	3.65
B	0.027	0.043	0.70	1.10
C	0.012	0.025	0.30	0.64
D	0.561	0.581	14.25	14.75
E	0.402	0.417	10.20	10.60
F	0.561	0.610	14.25	15.50
G	0.083	0.107	2.10	2.70
H	0.046	0.056	1.17	1.42
J	0.027	0.034	0.70	0.86
K	0.140	0.160	3.56	4.06

Case B-M (REV: R2)

R3 (25-February 2013)